



M1-M7 Schottky Rectifier

Feature

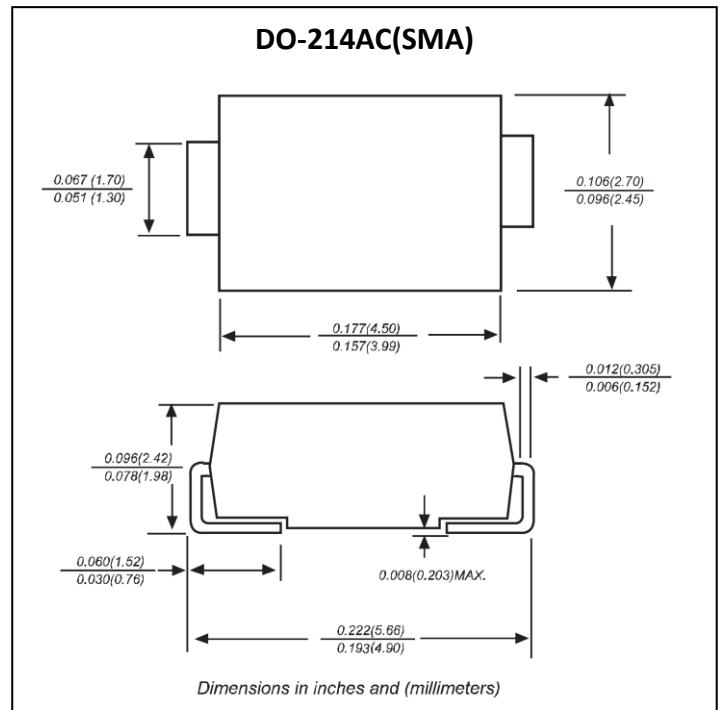
- I_o 1A
- V_{RRM} 50V-1000V
- Glass passivated chip
- High surge current capability

Application

- Rectifier

Marking

- MX: X From 1 to 7



ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	M							Unit
		1	2	3	4	5	6	7	
Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V_{RMS}	35	70	140	280	420	560	700	V
Average Forward Current (60HZ Half-sine wave, Resistance load, $T_a=75^\circ\text{C}$)	$I_{F(AV)}$	1							A
Non-repetitive Peak Forward Surge Current (60Hz Half-sine wave ,1 cycle , $T_a=25^\circ\text{C}$)	I_{FSM}	30							A
Junction Temperature	T_J	$-55 \sim +150$							$^\circ\text{C}$
Storage Temperature	T_{STG}	$-55 \sim +150$							$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition		MAX	Unit
Peak Forward Voltage	V_F	$I_F=1A$		1	V
Peak Reverse Current	I_{RRM1}	$V_{RM}=V_{RRM}$	$T_a=25^\circ\text{C}$	5	μA
	I_{RRM2}		$T_a=125^\circ\text{C}$	50	μA
Thermal Resistance(Typical)	$R_{\theta J-A}$	Between junction and ambient		55	$^\circ\text{C/W}$
	$R_{\theta J-L}$	Between junction and terminal		25	$^\circ\text{C/W}$

Typical Characteristics

